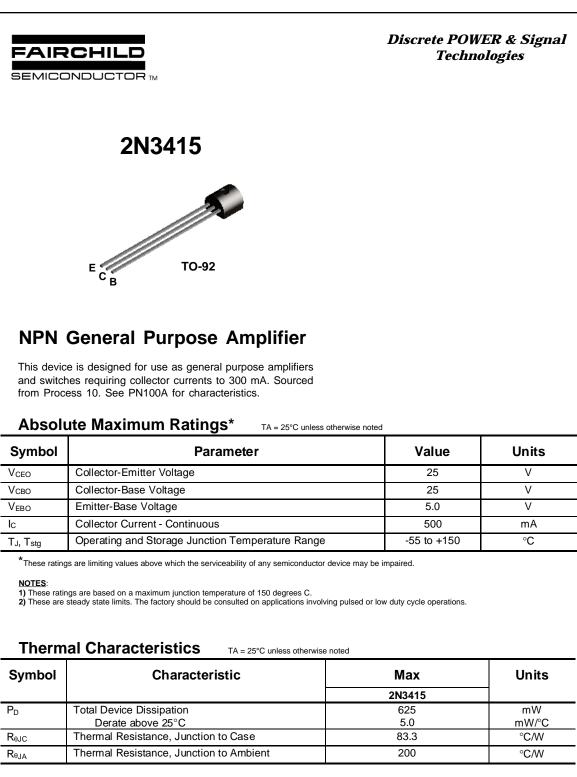
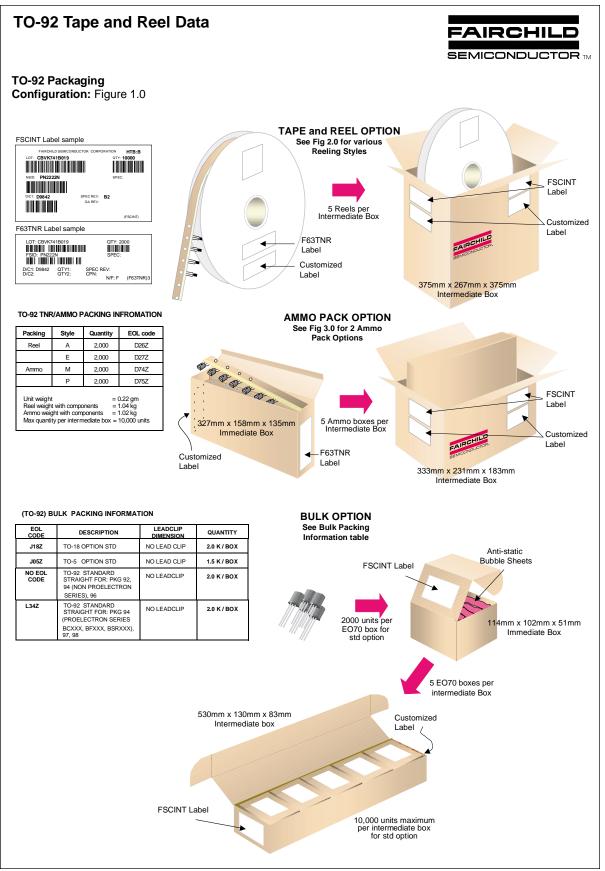
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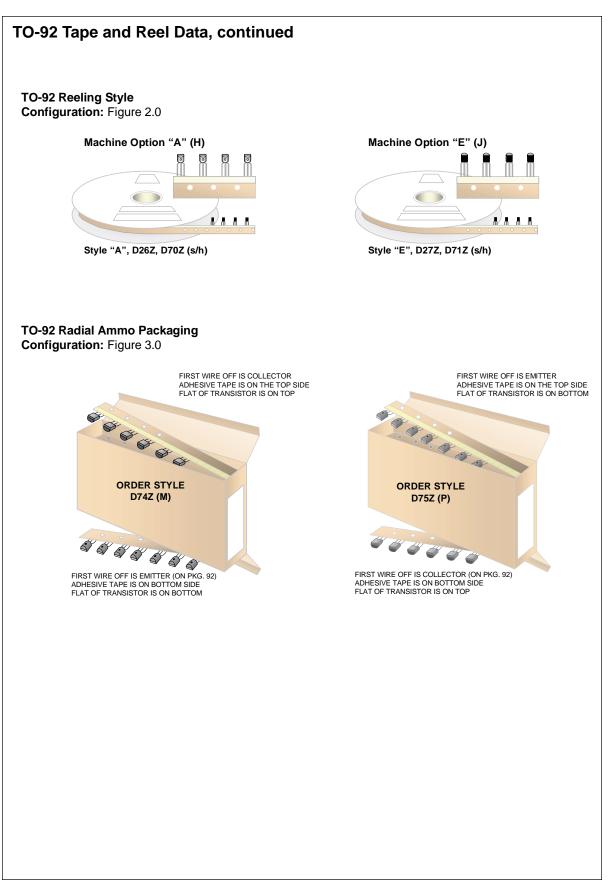
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$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage* $I_C = 10 \text{ mA}, I_B = 0$ 25V $V_{(BR)CBO}$ Collector-Base Breakdown Voltage $I_C = 10 \mu A, I_E = 0$ 25V $V_{(BR)EBO}$ Emitter-Base Breakdown Voltage $I_E = 10 \mu A, I_C = 0$ 5.0V CBO Collector-Cutoff Current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 μA CBO Emitter-Cutoff Current $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 μA CBO Emitter-Cutoff Current $V_{CB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA CBO Emitter-Cutoff Current $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICS N_{FE} Small-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, I_C = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 1801.3V	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Symbol	Parameter	Test Conditions	Min	Max	Units
Voltage*Voltage/(BR)CBOCollector-Base Breakdown Voltage $I_C = 10 \ \mu\text{A}, I_E = 0$ 25V/(BR)EBOEmitter-Base Breakdown Voltage $I_E = 10 \ \mu\text{A}, I_C = 0$ 5.0VCBOCollector-Cutoff Current $V_{CB} = 25 \ V, I_E = 0$ $V_{CB} = 25 \ V, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 μA EBOEmitter-Cutoff Current $V_{CB} = 25 \ V, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 μA EBOEmitter-Cutoff Current $V_{EB} = 5.0 \ V, I_C = 0$ 0.1 μA ON CHARACTERISTICS*ON CHARACTERISTICS $V_{CE} = 4.5 \ V, I_C = 2.0 \ m\text{A}$ 180540//CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \ m\text{A}, I_B = 3.0 \ m\text{A}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSNfeSmall-Signal Current Gain $I_C = 2.0 \ m\text{A}, V_{CE} = 4.5 \ V, I_C = 4.5 \ V, I_R = 3.0 \ m\text{A}$ 180180	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $		I				
Voltage*Image: Contract of the systemImage: Contract of the systemImage: Contract of the system(BR)CBOCollector-Base Breakdown VoltageIc = 10 μ A, Ic = 025V(BR)EBOEmitter-Base Breakdown VoltageIe = 10 μ A, Ic = 05.0V(BR)EBOCollector-Cutoff CurrentVcB = 25 V, Ie = 0 VcB = 25 V, Ie = 0, TA = 100°C0.1 μ A(BR)Emitter-Cutoff CurrentVcB = 25 V, Ie = 0, TA = 100°C0.1 μ A(BR)Emitter-Cutoff CurrentVcB = 5.0 V, Ic = 00.1 μ A(BR)Emitter-Cutoff CurrentVcE = 4.5 V, Ic = 2.0 mA180540(BC)Collector-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.3V(CE(sat))Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3V(BE(sat))Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3V(BE(sat))Base-Emitter Saturation VoltageIc = 1.0 kHz1801.3V	Voltage*Image: Contract of the systemImage: Contract of the systemImage: Contract of the system(BR)CBOCollector-Base Breakdown VoltageIc = 10 μ A, Ic = 025V(BR)EBOEmitter-Base Breakdown VoltageIe = 10 μ A, Ic = 05.0V(BR)EBOCollector-Cutoff CurrentVcB = 25 V, Ie = 0 VcB = 25 V, Ie = 0, TA = 100°C0.1 μ A(BR)Emitter-Cutoff CurrentVcB = 25 V, Ie = 0, TA = 100°C0.1 μ A(BR)Emitter-Cutoff CurrentVcB = 5.0 V, Ic = 00.1 μ A(BR)Emitter-Cutoff CurrentVcE = 4.5 V, Ic = 2.0 mA180540(BC)Collector-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.3V(CE(sat))Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3V(BE(sat))Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3V(BE(sat))Base-Emitter Saturation VoltageIc = 1.0 kHz1801.3V	Voltage*Image: Contract of the systemImage: Contract of the systemImage: Contract of the system(BR)CBOCollector-Base Breakdown VoltageIc = 10 μ A, Ic = 025V(BR)EBOEmitter-Base Breakdown VoltageIe = 10 μ A, Ic = 05.0V(BR)EBOCollector-Cutoff CurrentVcB = 25 V, Ie = 0 VcB = 25 V, Ie = 0, TA = 100°C0.1 μ A(BR)Emitter-Cutoff CurrentVcB = 25 V, Ie = 0, TA = 100°C0.1 μ A(BR)Emitter-Cutoff CurrentVcB = 5.0 V, Ic = 00.1 μ A(BR)Emitter-Cutoff CurrentVcE = 4.5 V, Ic = 2.0 mA180540(BC)Collector-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.3V(CE(sat))Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3V(BE(sat))Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3V(BE(sat))Base-Emitter Saturation VoltageIc = 1.0 kHz1801.3V	Voltage*Image: Control of the systemImage: Control						
IdeR)CBOCollector-Base Breakdown VoltageIc = 10 μ A, Ic = 025V(BR)EBOEmitter-Base Breakdown VoltageIe = 10 μ A, Ic = 05.0V(BR)EBOCollector-Cutoff CurrentVCB = 25 V, Ie = 0 VCB = 25 V, Ie = 0, TA = 100°C0.1 μ ABOEmitter-Cutoff CurrentVEB = 5.0 V, Ic = 00.1 μ ABOEmitter-Cutoff CurrentVEB = 5.0 V, Ic = 00.1 μ ACHARACTERISTICS*FEDC Current GainVCE = 4.5 V, Ic = 2.0 mA180540CE(sat)Collector-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.3VBase-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, VCE = 4.5 V, f = 1.0 kHz1801.3V	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	(BR)CEO		$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	25		V
BOCollector-Cutoff Current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 15 μA μA BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBase-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, I_B = 1.0 \text{ kHz}$ 180180	BOCollector-Cutoff Current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 15 μA μA BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBBSE-Emitter Saturation VoltageIc = 50 mA, I_B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, $V_{CE} = 4.5 \text{ V}, I_C = 4.5 \text{ V}, I_B = 1.0 \text{ kHz}$	BOCollector-Cutoff Current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 15 μA μA BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBBSE-Emitter Saturation VoltageIc = 50 mA, I_B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, $V_{CE} = 4.5 \text{ V}, I_C = 4.5 \text{ V}, I_B = 1.0 \text{ kHz}$	BOCollector-Cutoff Current $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 0.1 15 μA μA BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBBSE-Emitter Saturation VoltageIc = 50 mA, I_B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, $V_{CE} = 4.5 \text{ V}, I_C = 4.5 \text{ V}, I_B = 1.0 \text{ kHz}$	(BR)CBO		$I_{C} = 10 \ \mu A, \ I_{E} = 0$	25		V
$V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ 15 μA BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CelesatiCollector-Emitter Saturation VoltageIc = 50 mA, I_B = 3.0 mA0.3VSmall-Signal Current GainI_C = 2.0 mA, V_{CE} = 4.5 V,feSmall-Signal Current GainI_C = 2.0 mA, V_{CE} = 4.5 V,180feSmall-Signal Current GainI_C = 2.0 mA, V_{CE} = 4.5 V,180feSmall-Signal Current GainI_C = 2.0 mA, V_{CE} = 4.5 V,180	V _{CB} = 25 V, I _E = 0, T _A = 100°C15 μ ABOEmitter-Cutoff CurrentV _{EB} = 5.0 V, I _C = 00.1 μ AON CHARACTERISTICS*FEDC Current GainV _{CE} = 4.5 V, I _C = 2.0 mA180540Ce(sat)Collector-Emitter Saturation VoltageIc = 50 mA, I _B = 3.0 mA0.3VBE(sat)Base-Emitter Saturation VoltageIc = 50 mA, I _B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, V _{CE} = 4.5 V, f = 1.0 kHz	V _{CB} = 25 V, I _E = 0, T _A = 100°C15 μ ABOEmitter-Cutoff CurrentV _{EB} = 5.0 V, I _C = 00.1 μ AON CHARACTERISTICS*FEDC Current GainV _{CE} = 4.5 V, I _C = 2.0 mA180540Ce(sat)Collector-Emitter Saturation VoltageIc = 50 mA, I _B = 3.0 mA0.3VBE(sat)Base-Emitter Saturation VoltageIc = 50 mA, I _B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, V _{CE} = 4.5 V, f = 1.0 kHz	V _{CB} = 25 V, I _E = 0, T _A = 100°C15 μ ABOEmitter-Cutoff CurrentV _{EB} = 5.0 V, I _C = 00.1 μ AON CHARACTERISTICS*FEDC Current GainV _{CE} = 4.5 V, I _C = 2.0 mA180540Ce(sat)Collector-Emitter Saturation VoltageIc = 50 mA, I _B = 3.0 mA0.3VBE(sat)Base-Emitter Saturation VoltageIc = 50 mA, I _B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIc = 2.0 mA, V _{CE} = 4.5 V, f = 1.0 kHz	(BR)EBO			5.0		V
EBOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*IFEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540OreganCollector-Emitter Saturation VoltageI_C = 50 mA, I_B = 3.0 mA0.3VBase-Emitter Saturation VoltageI_C = 50 mA, I_B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICSIfeSmall-Signal Current GainI_C = 2.0 mA, V_{CE} = 4.5 V, from the second sec	BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBE(sat)Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSIeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180180	BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBE(sat)Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSIeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180180	BOEmitter-Cutoff Current $V_{EB} = 5.0 \text{ V}, I_C = 0$ 0.1 μA ON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540CE(sat)Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3VBE(sat)Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSIeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180180	СВО	Collector-Cutoff Current				
DN CHARACTERISTICS* FE DC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180 540 $I_{CE(sat)}$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3 V $Base-Emitter Saturation Voltage$ $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS fe Small-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, \\ f = 1.0 \text{ kHz}$ 180 180	ON CHARACTERISTICS* FE DC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180 540 CE(sat) Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3 V BE(sat) Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS Ic = 2.0 mA, V_{CE} = 4.5 V, f = 1.0 \text{ kHz} 180 180 180 180	ON CHARACTERISTICS* FE DC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180 540 CE(sat) Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3 V BE(sat) Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS Ic = 2.0 mA, V_{CE} = 4.5 V, f = 1.0 \text{ kHz} 180 180 180 180	ON CHARACTERISTICS* FE DC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180 540 CE(sat) Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3 V BE(sat) Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS Ic = 2.0 mA, V_{CE} = 4.5 V, f = 1.0 \text{ kHz} 180 180 180 180	BO	Emitter-Cutoff Current	$V_{CB} = 25 \text{ V}, I_E = 0, I_A = 100 \text{ C}$ $V_{EB} = 5.0 \text{ V}, I_C = 0$			
IFEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $V_{CE(sat)}$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSIfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180	FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $BE(sat)$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180	FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $BE(sat)$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180	FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $BE(sat)$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180		I				·
IFE DC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $V_{CE(sat)}$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSIfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180	FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $BE(sat)$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180180	FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $BE(sat)$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180180	FEDC Current Gain $V_{CE} = 4.5 \text{ V}, I_C = 2.0 \text{ mA}$ 180540 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.3V $BE(sat)$ Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 3.0 \text{ mA}$ 0.61.3VSMALL SIGNAL CHARACTERISTICSfeSmall-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V}, f = 1.0 \text{ kHz}$ 180180	ON CHAR	ACTERISTICS*				
Signal Base-Emitter Saturation Voltage Ic = 50 mA, IB = 3.0 mA 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS N_{fe} Small-Signal Current Gain Ic = 2.0 mA, V_{CE} = 4.5 V, fermion 180 $f = 1.0 \text{ kHz}$ Image: Note that the second	Base-Emitter Saturation Voltage Ic = 50 mA, I _B = 3.0 mA 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS Ic = 2.0 mA, V _{CE} = 4.5 V, f = 1.0 kHz 180 180 180	Base-Emitter Saturation Voltage Ic = 50 mA, I _B = 3.0 mA 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS Ic = 2.0 mA, V _{CE} = 4.5 V, f = 1.0 kHz 180 180 180	Base-Emitter Saturation Voltage Ic = 50 mA, I _B = 3.0 mA 0.6 1.3 V SMALL SIGNAL CHARACTERISTICS Ic = 2.0 mA, V _{CE} = 4.5 V, f = 1.0 kHz 180 180 180			$V_{CE} = 4.5 \text{ V}, I_{C} = 2.0 \text{ mA}$	180	540	
$V_{BE(sat)}$ Base-Emitter Saturation VoltageIc = 50 mA, I_B = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICS N_{fe} Small-Signal Current GainIc = 2.0 mA, V_{CE} = 4.5 V, fermionic fermi	Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICS feSmall-Signal Current GainIc = 2.0 mA, VCE = 4.5 V, f = 1.0 kHz180	Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICS feSmall-Signal Current GainIc = 2.0 mA, VCE = 4.5 V, f = 1.0 kHz180	Base-Emitter Saturation VoltageIc = 50 mA, IB = 3.0 mA0.61.3VSMALL SIGNAL CHARACTERISTICS feSmall-Signal Current GainIc = 2.0 mA, VCE = 4.5 V, f = 1.0 kHz180	1	Collector-Emitter Saturation Voltage	I _C = 50 mA, I _B = 3.0 mA		0.3	V
SMALL SIGNAL CHARACTERISTICS n_{fe} Small-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$ 180 $f = 1.0 \text{ kHz}$ 180	SMALL SIGNAL CHARACTERISTICS I_e Small-Signal Current Gain $I_c = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$ 180 $f = 1.0 \text{ kHz}$ $f = 1.0 \text{ kHz}$ 180	SMALL SIGNAL CHARACTERISTICS I_e Small-Signal Current Gain $I_c = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$ 180 $f = 1.0 \text{ kHz}$ $f = 1.0 \text{ kHz}$ 180	SMALL SIGNAL CHARACTERISTICS I_e Small-Signal Current Gain $I_c = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$ 180 $f = 1.0 \text{ kHz}$ $f = 1.0 \text{ kHz}$ 180	/CE(sat)	5			4.0	V
				(BE(sat) SMALL S fe	Base-Emitter Saturation Voltage	I _C = 2.0 mA, V _{CE} = 4.5 V,		1.3	
				(BE(sat) SMALL S fe	Base-Emitter Saturation Voltage	I _C = 2.0 mA, V _{CE} = 4.5 V,		1.3	
				/ _{BE(sat)} SMALL S _{Dfe}	Base-Emitter Saturation Voltage	I _C = 2.0 mA, V _{CE} = 4.5 V,			
				BE(sat)	Base-Emitter Saturation Voltage	I _C = 2.0 mA, V _{CE} = 4.5 V,			

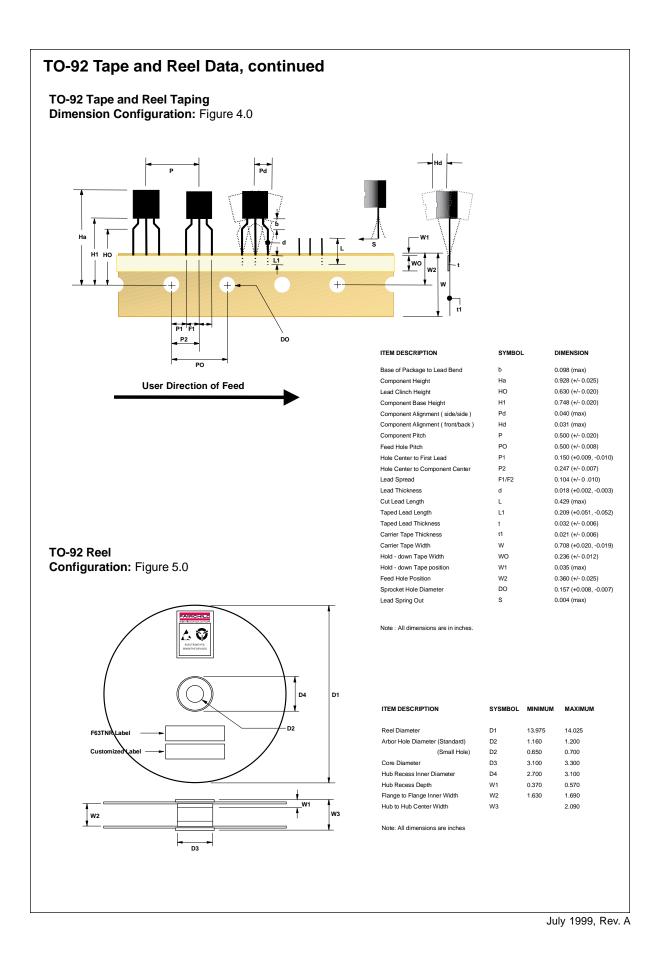


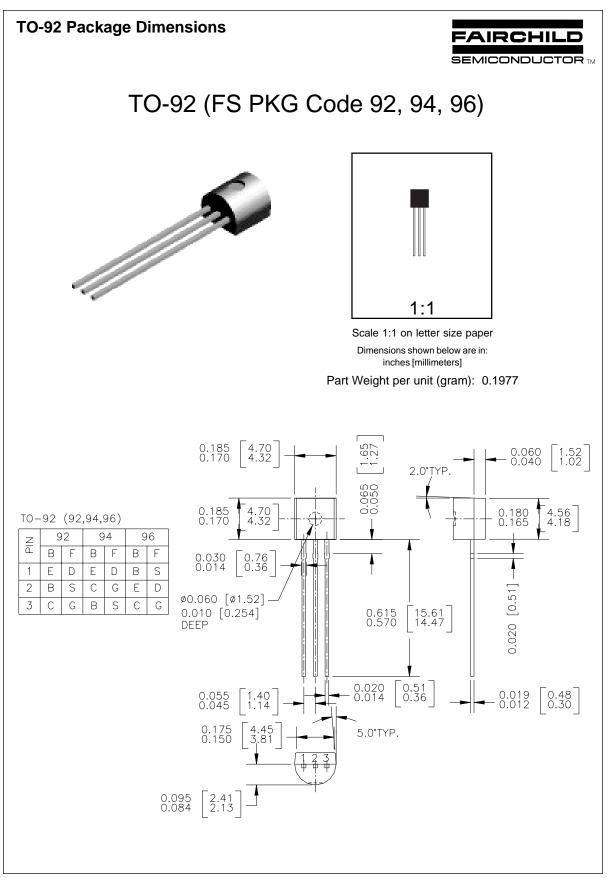
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